

Notice of References CitedApplication/Control No.
09/912,558Applicant(s)/Patent Under
Reexamination
WEIMER ET AL.Examiner
Erik KielinArt Unit
2813

Page 1 of 1

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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	C	US-2001/0020725	09-2001	Okuno et al.	257/410
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	L	US-			
	M	US-			

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Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.